

SOT223 PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR

ISSUE 2 – FEBRUARY 1995

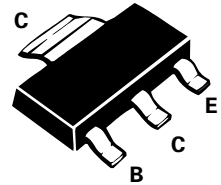
FEATURES

- * 400 Volt V_{CE0}
- * 0.5 Amp continuous current
- * Low saturation voltage

COMPLEMENTARY TYPE – FZT658

PARTMARKING DETAIL – FZT758

FZT758



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-400	V
Collector-Emitter Voltage	V_{CEO}	-400	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-1	A
Continuous Collector Current	I_C	-500	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	2	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-400		V	$I_C = -100\mu A$
Collector-Emitter Breakdown Voltage	$V_{CEO(SUS)}$	-400		V	$I_C = -10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		V	$I_E = -100\mu A$
Collector Cut-Off Current	I_{CBO}		-100	nA	$V_{CB} = -320V$
Collector Cut-Off Current	I_{CES}		-100	nA	$V_{CE} = -320V$
Emitter Cut-Off Current	I_{EBO}		-100	nA	$V_{EB} = -4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.30 -0.25 -0.50	V V V	$I_C = -20mA, I_B = -1mA$ $I_C = -50mA, I_B = -5mA^*$ $I_C = -100mA, I_B = -10mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-0.9	V	$I_C = -100mA, I_B = -10mA^*$
Base-Emitter Turn On Voltage	$V_{BE(on)}$		-1.0	V	$I_C = -100mA, V_{CE} = -5V^*$
Static Forward Current Transfer Ratio	h_{FE}	50 50 40			$I_C = -1mA, V_{CE} = -5V$ $I_C = -100mA, V_{CE} = -5V^*$ $I_C = -200mA, V_{CE} = -10V^*$
Transition Frequency	f_T	50		MHz	$I_C = -20mA, V_{CE} = -20V$ $f = 20MHz$
Output Capacitance	C_{obo}		20	pF	$V_{CB} = -20V, f = 1MHz$
Switching times	t_{on} t_{off}	140 2000	Typical Typical	ns ns	$I_C = -100mA, V_{CC} = -100V$ $I_{B1} = 10mA, I_{B2} = -20mA$

* Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

Spice parameter data is available upon request for this device

TYPICAL CHARACTERISTICS

